Application No. 10/683,727 INFORMATION DISCLOSURE Filing Date October 10, 2003 First Named Inventor Sherman STATEMENT BY APPLICANT Art Unit 1762 (Multiple sheets used when necessary) Examiner Kelly M. Stouffer SHEET 1 OF 1 Attorney Docket No. ASMMC.9CP1DV1C1

	U.S. PATENT DOCUMENTS									
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear					

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹		
/KMS/		20a-ZC-1, MIYAMOTO et al., "High-Fluidity Deposition of SiN by Cryogenic Remote Plasma CVD," Research Center for Integrated Systems and Faculty of Engineering, Hiroshima University, 1 page.	✓		
/KMS/		20a-ZC-2, GOTOU et al., "Atomic-Layer Deposition of SiN by Remote Plasma CVD," Research Center for Integrated Systems, Hiroshima University, 2 pages.	1		
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Examiner Signature /Kelly Stouffer/

Date Considered 07/17/2007

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.